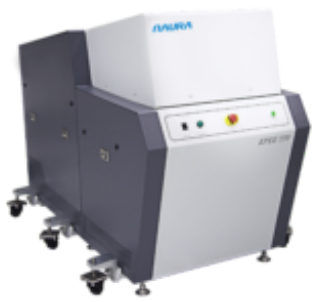
As LEDs get smaller and films get thinner, LED manufacturers need production-worthy process solutions for the high-speed deposition of uniform SiO2 (silicon dioxide), SiNx (silicon nitride) and SiOxNx (silicon oxynitride) films. NAURA Akrion's **EPEE 550 PECVD** (plasma enhanced chemical vapor deposition) product offers LED manufacturers a flexible PECVD tool that can accommodate a wide variety of substrate sizes with an affordable batch tool.

nt-emitting diode (LED) is a semiconductor light source that emits light when current flows through it. From the first low-intensity infrared LEDs used in remote control its, LEDs can now emit a wide variety of light colors with extreme efficiency and lifespans, serving a multitude of applications to include architectural/industrial/residential lighting, automotive head/tail lights, traffic signals, mobile/tablet/computer/TV displays, horticultural lamps and medical devices. The emerging mini/micro LED technology will serve as the cornerstone of next-generation display technology for products such as mobile phones, wearable watches, virtual/augmented reality, micro-projectors and ultrahigh-definition TVs.

EPEE 550 PECVD



EPEE 550 PECVD is used in the manufacturing of LED chips and composite substrates. It is widely used in the deposition of SiO and SiNx dielectric films for LED blue-green and red-yellow devices and the high-speed deposition of SiO thick films on patterned sapphire substrates (PSS). In addition, the EPEE 550 PECVD tool supports high uniformity and low stress SiNx thin film deposition which can be applied to the development and mass production of third-generation semiconductor power devices.

See More Information

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